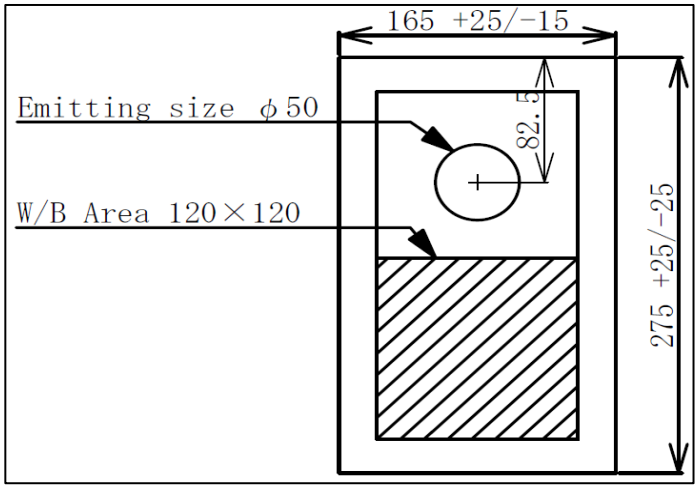
OPA8205PPS

φ50μm Infrared Pin-Point LED Chip

Unit : ㎛



1. Material

Substrate	GaAs	(N Type)
Epitaxial Layer	AlGaAs	(P/N Type)

2. Electrode

N(Cathode) Side Gold Alloy
P(Anode) Side Gold Alloy

3. Mechanical Data

3.1 Chip Size : 165㎛ X 275㎛
3.2 Emitting Window : φ50 ㎛
3.3 W/B Area : 120㎛ X 120㎛
3.4 Chip Thickness : 280 ㎛

4. Absolute Maximum Ratings

Ta=25℃

Parameter	Symbol	Rating	Unit
Power Dissipation	PD	125	mW
Forward Current	IF	50	mA
Reverse Voltage	VR	3	V
Operating Temperature	Topr	-20 ~ +85	℃
Storage Temperature	Tstg	-40 ~ +100	℃

5. Electro-Optical Characteristics

Ta=25℃

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	VF	IF=20mA	-	1.6	2	V
Reverse Current	IR	VR=3V	-	-	1	μA
Radiated Power※	Po	IF=20mA	0.23	0.6	-	mW
Peak Wavelength	λp	IF=20mA	-	820	-	nm

※ LED chip is mounted on TO-18 stem without resin coated.
Radiated Power is all light quantity that measured in integrating sphere owned by us.

AUK CORP.
Yakchon Factory, 62-21, 8, Yakchon-ro, Iksan, Korea
Tel. +82 63 839 1111 **Fax.** +82 63 835 8259
www.auk.co.kr

IATF16949 ISO14001